

## Dual/Quad SPST, CMOS Analog Switches

HI-200/HI-201 (dual/quad) are monolithic devices comprising independently selectable SPST switches which feature fast switching speeds (HI-200 240ns, and HI-201 185ns) combined with low power dissipation (15mW at 25°C). Each switch provides low "ON" resistance operation for input signal voltage up to the supply rails and for signal current up to 80mA. Rugged DI construction eliminates latch-up and substrate SCR failure modes.

All devices provide break-before-make switching and are TTL and CMOS compatible for maximum application versatility. HI-200/HI-201 are ideal components for use in high frequency analog switching. Typical applications include signal path switching, sample and hold circuit, digital filters, and operational amplifier gain switching networks.

## Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HI3-0200-5Z (Note)	0 to 75	14 Ld PDIP* (Pb-free)	E14.3
HI1-0201-2	-55 to 125	16 Ld CERDIP	F16.3
HI1-0201-4	-25 to 85	16 Ld CERDIP	F16.3
HI1-0201-5	0 to 75	16 Ld CERDIP	F16.3
HI3-0201-5	0 to 75	16 Ld PDIP	E16.3
HI3-0201-5Z (Note)	0 to 75	16 Ld PDIP* (Pb-free)	E16.3
HI4P0201-5	0 to 75	20 Ld PLCC	N20.35
HI4P0201-5Z (Note)	0 to 75	20 Ld PLCC (Pb-free)	N20.35
HI9P0201-5	0 to 75	16 Ld SOIC	M16.15
HI9P0201-5Z (Note)	0 to 75	16 Ld SOIC (Pb-free)	M16.15
HI9P0201-9	-40 to 85	16 Ld SOIC	M16.15
HI9P0201-9Z (Note)	-40 to 85	16 Ld SOIC (Pb-free)	M16.15

\*Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020. Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

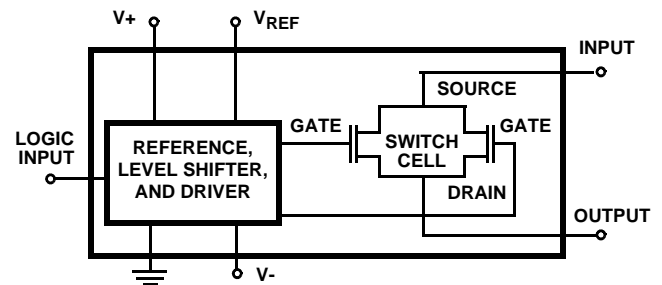
## Features

- Pb-Free Available (RoHS Compliant)
- Analog Voltage Range . . . . . ±15V
- Analog Current Range . . . . . 80mA
- Turn-On Time . . . . . 240ns
- Low  $r_{ON}$  . . . . . 55Ω
- Low Power Dissipation . . . . . 15mW
- TTL/CMOS Compatible

## Applications

- High Frequency Analog Switching
- Sample and Hold Circuits
- Digital Filters
- Operational Amplifier Gain Switching Networks

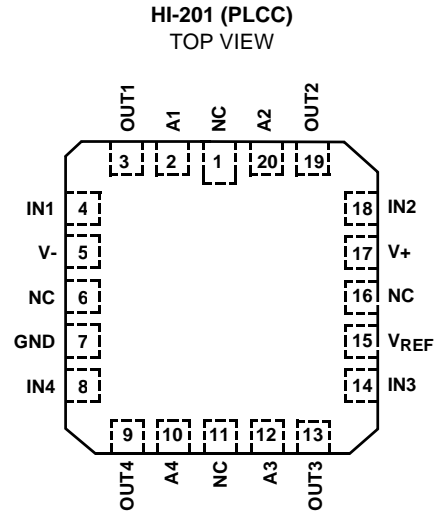
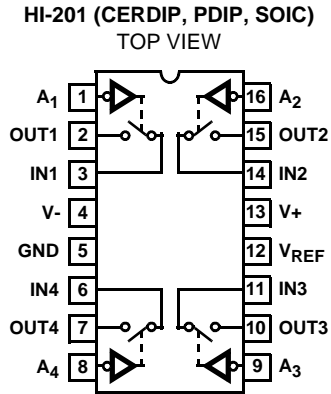
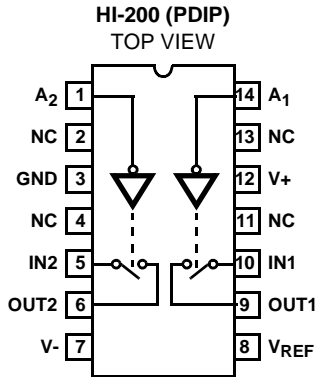
## Functional Diagram



TRUTH TABLE

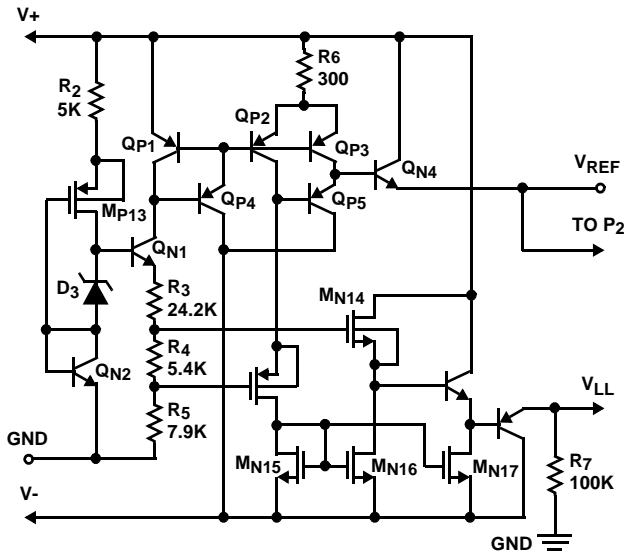
LOGIC	HI-200	HI-201
0	ON	ON
1	OFF	OFF

**Pinouts** (Switches Shown For Logic "1" Input)

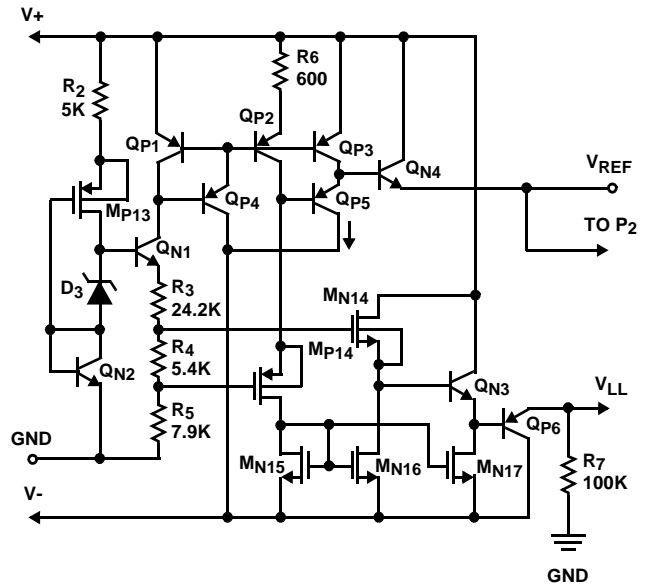


**Schematic Diagrams**

TTL/CMOS REFERENCE CIRCUIT  $V_{REF}$  CELL  
HI-200

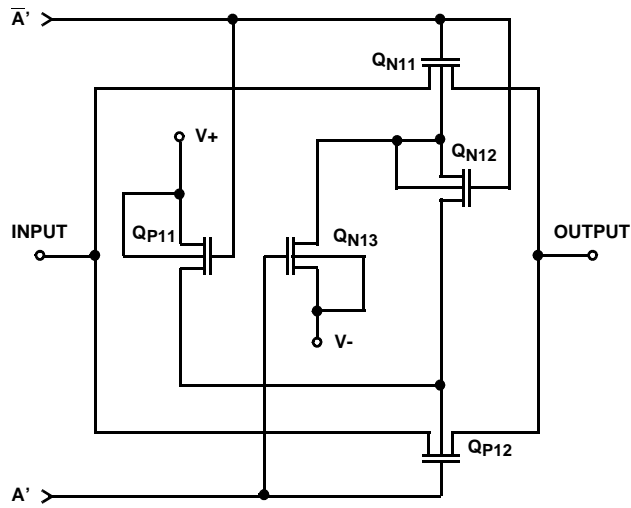


TTL/CMOS REFERENCE CIRCUIT  $V_{REF}$  CELL  
HI-201

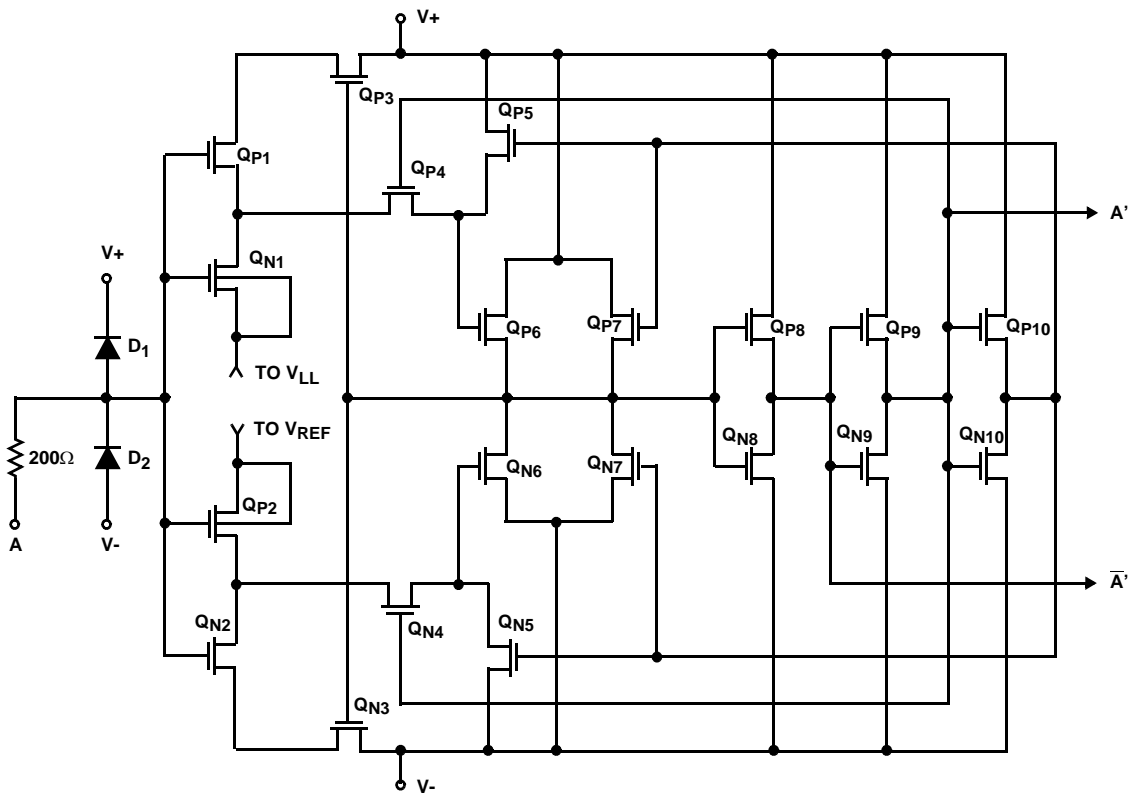


Schematic Diagrams (Continued)

SWITCH CELL



DIGITAL INPUT BUFFER AND LEVEL SHIFTER



# HI-200, HI-201

## Absolute Maximum Ratings

Supply Voltage (V+ to V-) .....	44V (±22)
V <sub>REF</sub> to Ground .....	20V, -5V
Digital Input Voltage .....	(V+) +4V to (V-) -4V
Analog Input Voltage (One Switch) .....	(V+) +2V to (V-) -2V

## Operating Conditions

Temperature Ranges	
HI-201-2 .....	-55°C to 125°C
HI-201-4 .....	-25°C to 85°C
HI-200-5, HI-201-5 .....	0°C to 75°C
HI-201-9 .....	-40°C to 85°C

## Thermal Information

Thermal Resistance (Typical, Note 1)	$\theta_{JA}$ (°C/W)	$\theta_{JC}$ (°C/W)
CERDIP Package .....	75	20
PLCC Package .....	80	N/A
PDIP Package* .....	95	N/A
SOIC Package .....	110	N/A
Maximum Storage Temperature .....	-65°C to 150°C	
Maximum Junction Temperature (Hermetic Packages) .....	175°C	
Maximum Junction Temperature (Plastic Packages) .....	150°C	
Maximum Lead Temperature (Soldering, 10s) .....	300°C (PLCC and SOIC - Lead Tips Only)	

\*Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in reflow solder processing applications.

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTE:

- $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## Electrical Specifications

Supplies = +15V, -15V; V<sub>REF</sub> = Open; V<sub>AH</sub> (Logic Level High) = 2.4V, V<sub>AL</sub> (Logic Level Low) = 0.8V

PARAMETER	TEST CONDITIONS	TEMP (°C)	-2			-4, -5, -9			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
<b>DYNAMIC CHARACTERISTICS</b>									
Switch ON Time, t <sub>ON</sub>									
HI-200		25	-	240	500	-	240	-	ns
HI-201		25	-	185	500	-	185	-	ns
		Full	-	1000	-	-	1000	-	ns
Switch OFF Time, t <sub>OFF</sub>									
HI-200		25	-	330	500	-	500	-	ns
HI-201		25	-	220	500	-	220	-	ns
		Full	-	1000	-	-	1000	-	ns
Off Isolation	(Note 4)								
HI-200		25	-	70	-	-	70	-	dB
HI-201		25	-	80	-	-	80	-	dB
Input Switch Capacitance, C <sub>S(OFF)</sub>		25	-	5.5	-	-	5.5	-	pF
Output Switch Capacitance, C <sub>D(OFF)</sub>		25	-	5.5	-	-	5.5	-	pF
Output Switch Capacitance, C <sub>D(ON)</sub>		25	-	11	-	-	11	-	pF
Digital Input Capacitance, C <sub>A</sub>		25	-	5	-	-	5	-	pF
Drain-to-Source Capacitance, C <sub>DS(OFF)</sub>		25	-	0.5	-	-	0.5	-	pF
<b>DIGITAL INPUT CHARACTERISTICS</b>									
Input Low Threshold, V <sub>AL</sub>		Full	-	-	0.8	-	-	0.8	V
Input High Threshold, V <sub>AH</sub>		Full	2.4	-	-	2.4	-	-	V
Input Leakage Current (High or Low), I <sub>A</sub>	(Note 3)	Full	-	-	1.0	-	-	1.0	μA
<b>ANALOG SWITCH CHARACTERISTICS</b>									
Analog Signal Range, V <sub>S</sub>		Full	-15	-	+15	-15	-	+15	V
ON Resistance, r <sub>ON</sub>	(Note 2)	25	-	55	70	-	55	80	Ω
		Full	-	80	100	-	72	100	Ω

# HI-200, HI-201

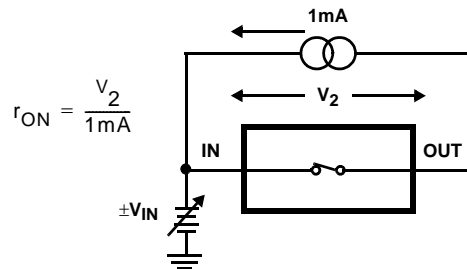
## Electrical Specifications Supplies = +15V, -15V; V<sub>REF</sub> = Open; V<sub>AH</sub> (Logic Level High) = 2.4V, V<sub>AL</sub> (Logic Level Low) = 0.8V (Continued)

PARAMETER	TEST CONDITIONS	TEMP (°C)	-2			-4, -5, -9			UNITS	
			MIN	TYP	MAX	MIN	TYP	MAX		
OFF Input Leakage Current, I <sub>S(OFF)</sub>	(Note 6)	25	-	1	5	-	1	50	nA	
		Full	-	100	500	-	10	500	nA	
		HI-200	25	-	2	5	-	2	50	nA
		HI-201	Full	-	-	500	-	-	250	nA
OFF Output Leakage Current, I <sub>D(OFF)</sub>	(Note 6)	25	-	1	5	-	1	50	nA	
		Full	-	100	500	-	10	500	nA	
		HI-200	25	-	2	5	-	2	50	nA
		HI-201	Full	-	35	500	-	35	250	nA
ON Leakage Current, I <sub>D(ON)</sub>	(Note 6)	25	-	1	5	-	1	50	nA	
		Full	-	100	500	-	10	500	nA	
		HI-200	25	-	2	5	-	2	50	nA
		HI-201	Full	-	-	500	-	-	250	nA
<b>POWER SUPPLY CHARACTERISTICS</b> (Note 5)										
Power Dissipation, P <sub>D</sub>		25	-	15	-	-	15	-	mW	
		Full	-	-	60	-	-	60	mW	
Current, I <sub>+</sub>		25	-	0.5	-	-	0.5	-	mA	
		Full	-	-	2.0	-	-	2.0	mA	
Current, I <sub>-</sub>		25	-	0.5	-	-	0.5	-	mA	
		Full	-	-	2.0	-	-	2.0	mA	

**NOTES:**

- V<sub>OUT</sub> = ±10V, I<sub>OUT</sub> = 1mA.
- Digital Inputs are MOS gates: typical leakage is < 1nA.
- V<sub>A</sub> = 5V, R<sub>L</sub> = 1kΩ, C<sub>L</sub> = 10pF, V<sub>S</sub> = 3V<sub>RMS</sub>, f = 100kHz.
- V<sub>A</sub> = +3V or V<sub>A</sub> = 0V for Both Switches.
- V<sub>A</sub> = +3V or V<sub>A</sub> = 0V for Both Switches.
- Refer to Leakage Current Measurements (Figure 2).

## Test Circuits and Waveforms T<sub>A</sub> = 25°C, V<sub>SUPPLY</sub> = ±15V, V<sub>AH</sub> = 2.4V, V<sub>AL</sub> = 0.8V and V<sub>REF</sub> = Open



**FIGURE 1A. ON RESISTANCE TEST CIRCUIT**

**Test Circuits and Waveforms**  $T_A = 25^\circ\text{C}$ ,  $V_{\text{SUPPLY}} = \pm 15\text{V}$ ,  $V_{\text{AH}} = 2.4\text{V}$ ,  $V_{\text{AL}} = 0.8\text{V}$  and  $V_{\text{REF}} = \text{Open}$  (Continued)

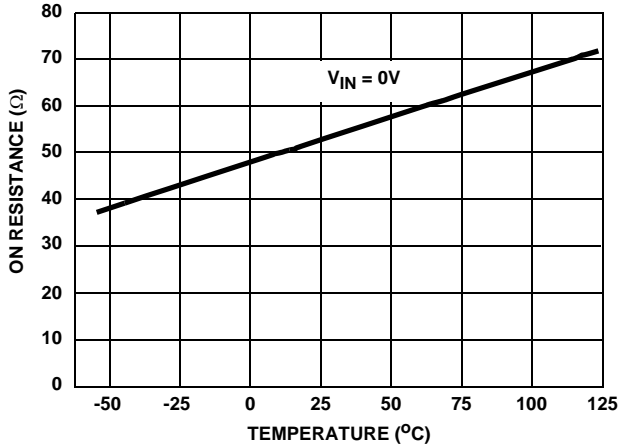


FIGURE 1B. ON RESISTANCE vs TEMPERATURE

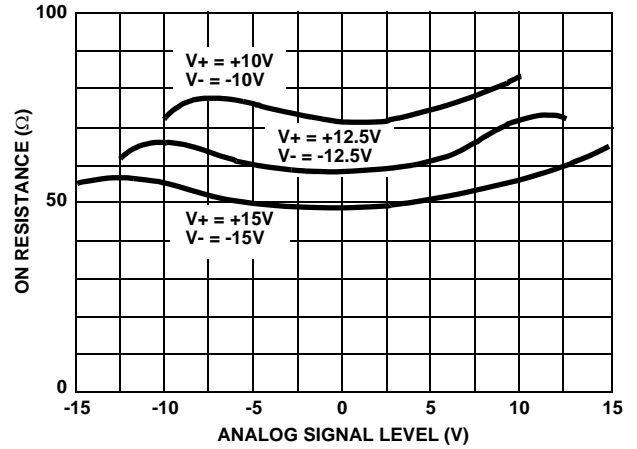


FIGURE 1C. HI-200 ON RESISTANCE vs ANALOG SIGNAL LEVEL

FIGURE 1. ON RESISTANCE

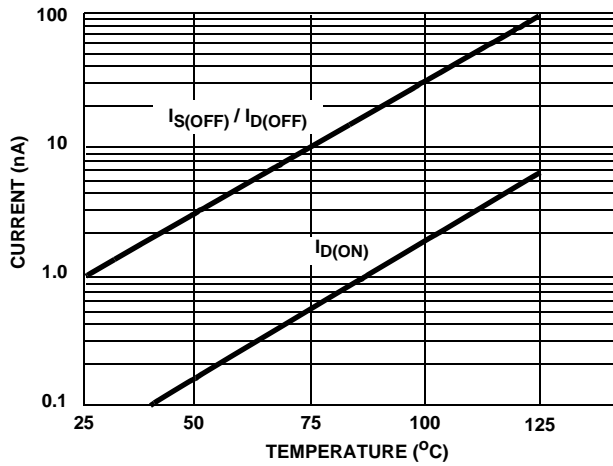


FIGURE 2A. LEAKAGE CURRENT vs TEMPERATURE

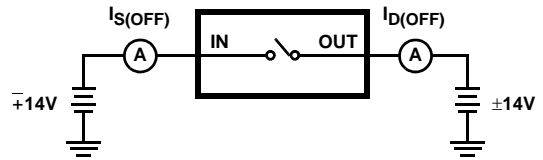


FIGURE 2B. OFF LEAKAGE CURRENT TEST CIRCUIT

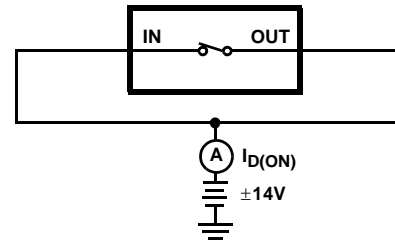


FIGURE 2C. ON LEAKAGE CURRENT TEST CIRCUIT

FIGURE 2. LEAKAGE CURRENTS

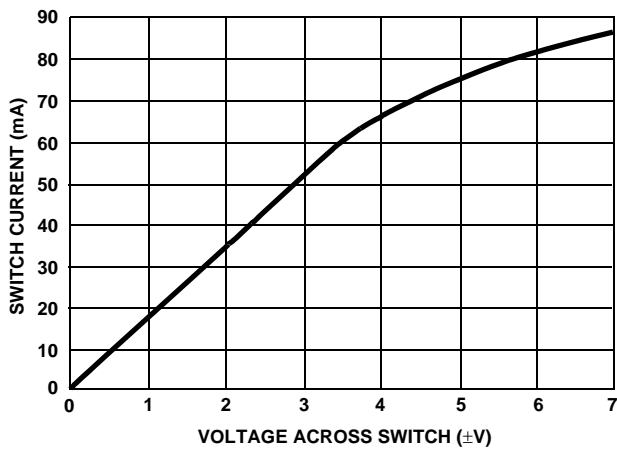


FIGURE 3A. SWITCH CURRENT vs VOLTAGE

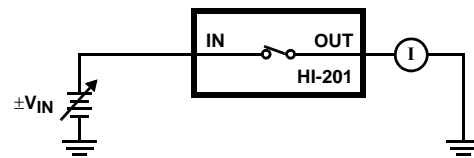


FIGURE 3B. TEST CIRCUIT

FIGURE 3. SWITCH CURRENT

**Test Circuits and Waveforms**  $T_A = 25^{\circ}\text{C}$ ,  $V_{\text{SUPPLY}} = \pm 15\text{V}$ ,  $V_{\text{AH}} = 2.4\text{V}$ ,  $V_{\text{AL}} = 0.8\text{V}$  and  $V_{\text{REF}} = \text{Open}$  (Continued)

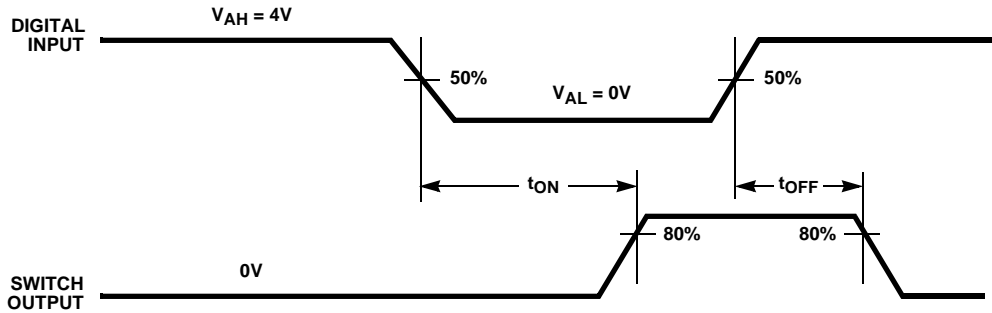


FIGURE 4A. MEASUREMENT POINTS

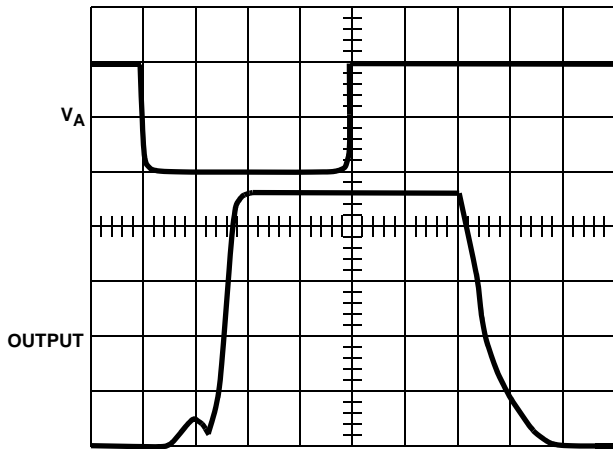


FIGURE 4B. WAVEFORMS WITH TTL COMPATIBLE LOGIC INPUT

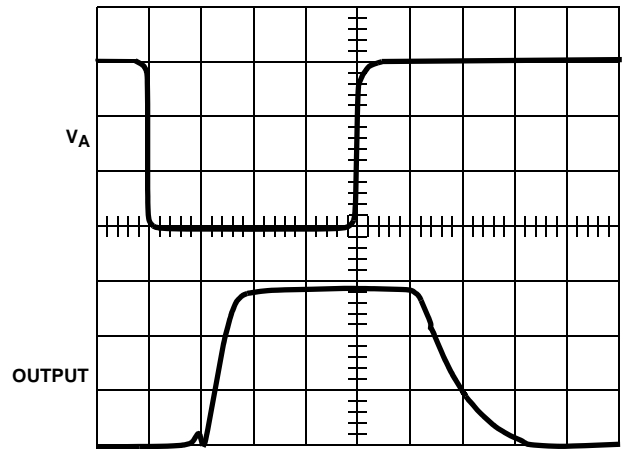


FIGURE 4C. WAVEFORMS WITH CMOS COMPATIBLE LOGIC INPUT

FIGURE 4. SWITCH  $t_{\text{ON}}$  AND  $t_{\text{OFF}}$

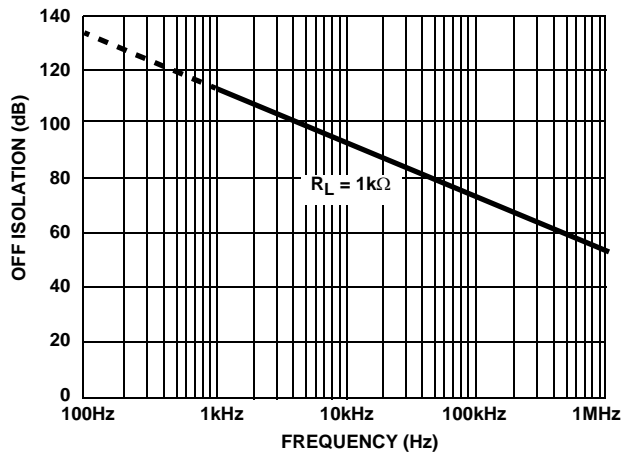


FIGURE 5. HI-201 OFF ISOLATION vs FREQUENCY

For more information see Application Notes AN520, AN521, AN531, AN532 and AN557.

## ***Application Information***

### ***Single Supply Operation***

The switch operation of the HI-200/201 is dependent upon an internally generated switching threshold voltage optimized for  $\pm 15\text{V}$  power supplies. The HI-200/201 does not provide the necessary internal switching threshold in a single supply system. Therefore, if single supply operation is required, the HI-300 series of switches is recommended. The HI-300 series will remain operational to a minimum +5V single supply.

Switch performance will degrade as power supply voltage is reduced from optimum levels ( $\pm 15\text{V}$ ). So it is recommended that a single supply design be thoroughly evaluated to ensure that the switch will meet the requirements of the application.

For further information see Application Notes AN520, AN557, AN1033 and AN1034.



**Die Characteristics**

**METALLIZATION:**

Type: CuAl  
 Thickness:  $16\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

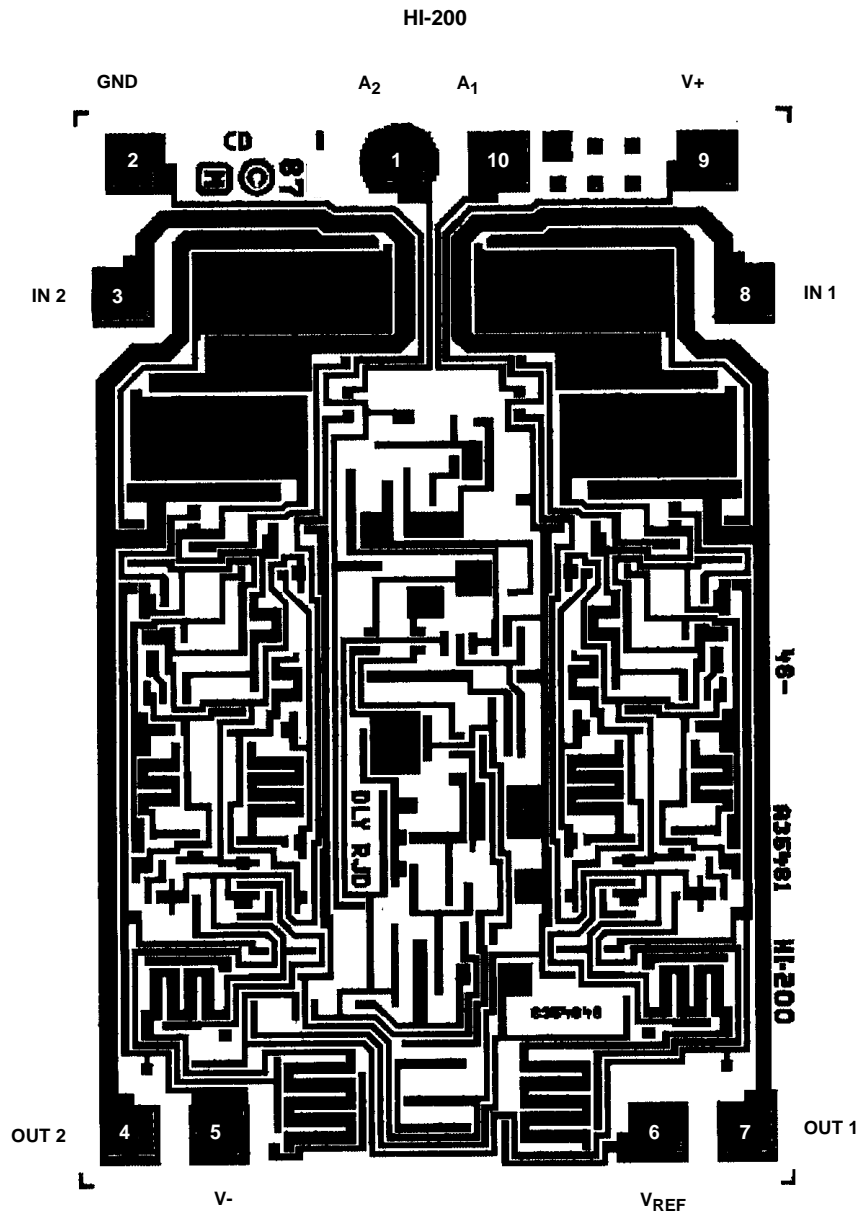
**PASSIVATION:**

Type: Nitride over Silox  
 Nitride Thickness:  $3.5\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$   
 Silox Thickness:  $12\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

**WORST CASE CURRENT DENSITY:**

$2 \times 10^5 \text{ A/cm}^2$  at 25mA

**Metallization Mask Layout**



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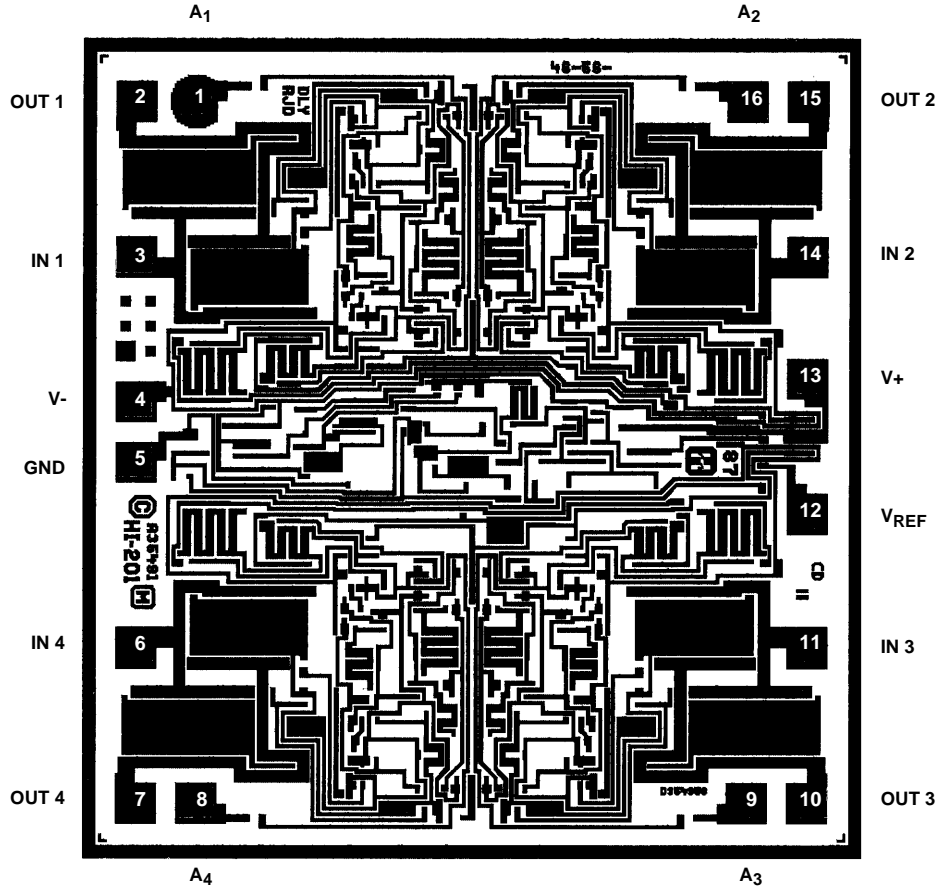
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**Metallization Mask Layout**

HI-201



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